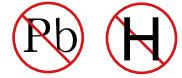




YEA SHIN TECHNOLOGY CO., LTD

YS3812VBB

Dual N-Channel Enhancement MOSFET



VDS= 30V, ID= 20A

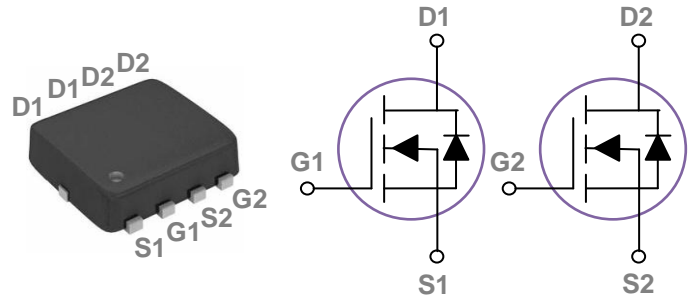
Features

- 30V,20A, $R_{DS(ON)} = 20m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

PPAK3x3 Dual Pin Configuration



Absolute Maximum Rating $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ C$)	20	A
	Drain Current – Continuous ($T_c=100^\circ C$)	13	A
I_{DM}	Drain Current – Pulsed ¹	80	A
EAS	Single Pulse Avalanche Energy ²	14	mJ
IAS	Single Pulse Avalanche Current ²	17	A
P_D	Power Dissipation ($T_c=25^\circ C$)	20	W
	Power Dissipation – Derate above $25^\circ C$	0.16	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	6.4	$^\circ C/W$

DEVICE CHARACTERISTICS

YS3812VBB

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.04	---	$V/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-source On-Resistance ³	$V_{GS}=10V, I_D=10A$	---	17	20	$m\Omega$
		$V_{GS}=4.5V, I_D=6A$	---	23	30	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	$mV/^\circ\text{C}$
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=6A$	---	13	---	S

Dynamic and Switching Characteristics

Q_g	Total Gate Charge ^{3,4}	$V_{DS}=15V, V_{GS}=4.5V, I_D=8A$	---	4.1	6	nC
Q_{gs}	Gate-Source Charge ^{3,4}		---	1	1.4	
Q_{gd}	Gate-Drain Charge ^{3,4}		---	2.1	4	
$T_{d(on)}$	Turn-On Delay Time ^{3,4}	$V_{DD}=15V, V_{GS}=10V, R_G=6\Omega, I_D=1A$	---	2.8	5	ns
T_r	Rise Time ^{3,4}		---	7.2	14	
$T_{d(off)}$	Turn-Off Delay Time ^{3,4}		---	15.8	30	
T_f	Fall Time ^{3,4}		---	4.6	9	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	---	345	500	pF
C_{oss}	Output Capacitance		---	55	80	
C_{rss}	Reverse Transfer Capacitance		---	32	55	
R_g	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	---	3.2	5.6	Ω

Drain-Source Diode Characteristics and Maximum Ratings

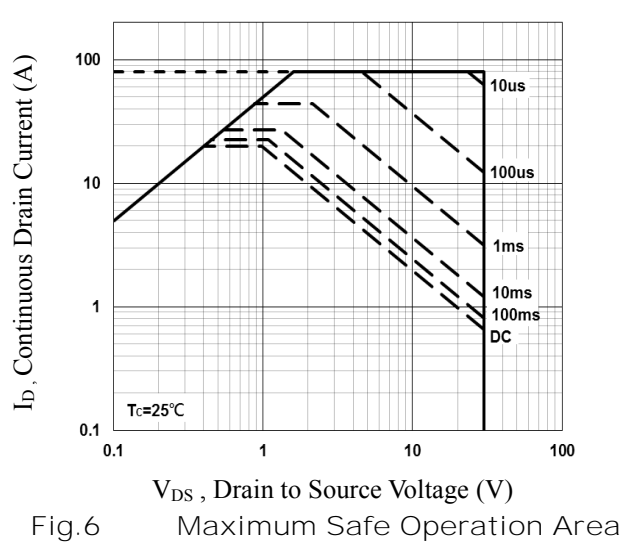
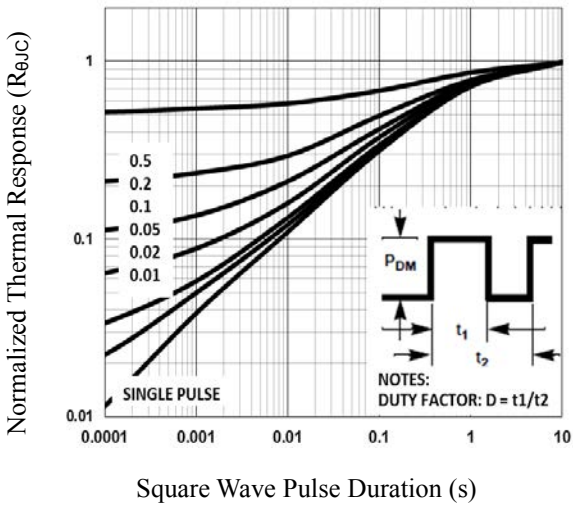
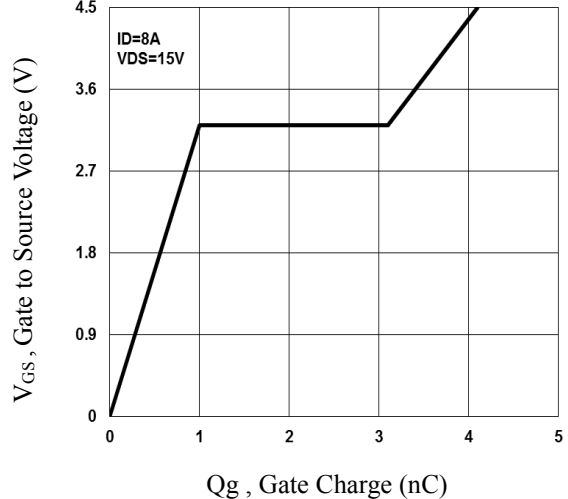
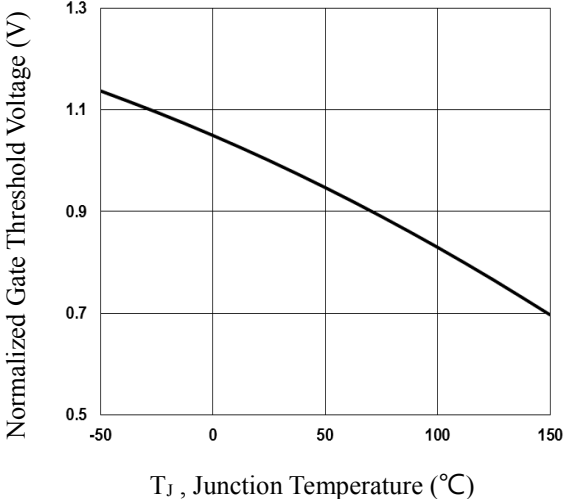
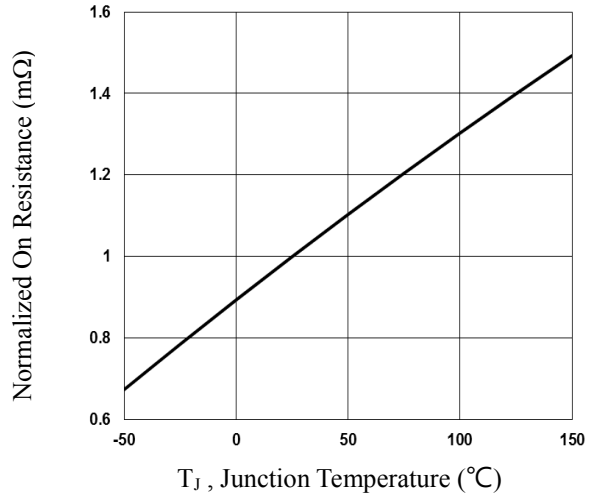
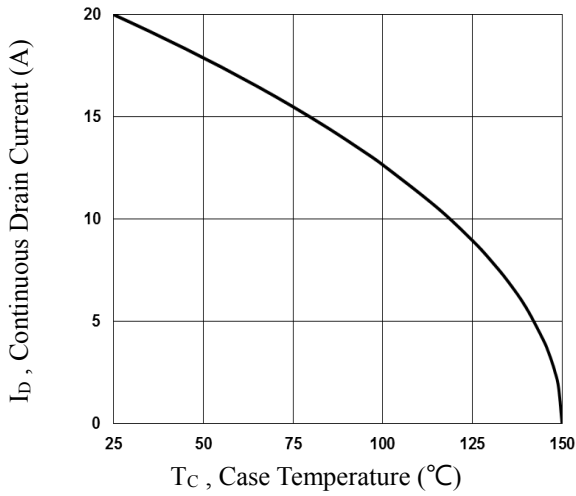
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V, \text{Force Current}$	---	---	20	A
I_{SM}	Pulsed Source Current ³		---	---	80	A
V_{SD}	Diode Forward Voltage ³	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_S=1A, di/dt=100A/\mu s$	---	8.37	---	ns
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	2.08	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=17A, R_G=25\Omega, \text{Starting } T_J=25^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

DEVICE CHARACTERISTICS

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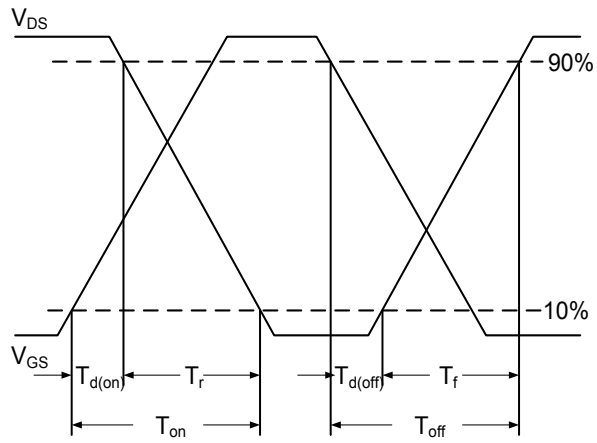


Fig.7 Switching Time Waveform

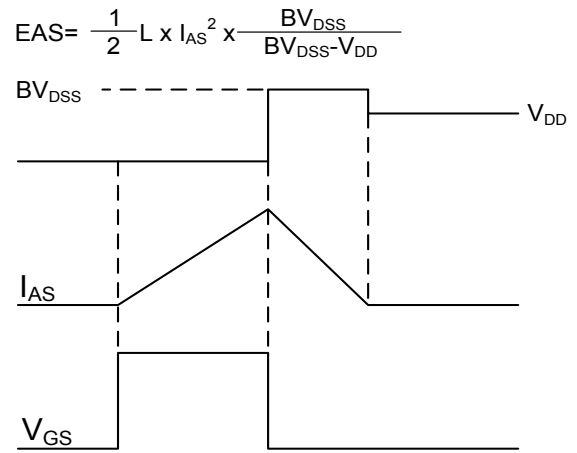
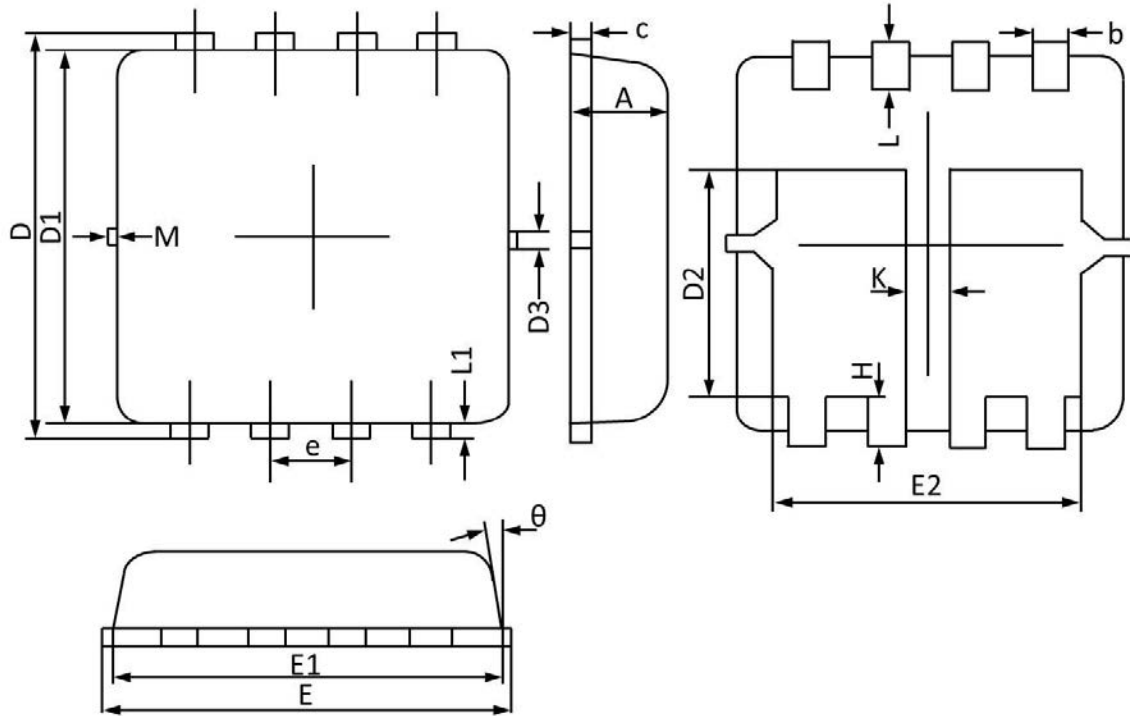


Fig.8 EAS Waveform

PACKAGE OUTLINE & DIMENSIONS

YS3812VBB

PPAK3x3 Dual PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
b	0.250	0.350	0.010	0.013
c	0.100	0.250	0.004	0.009
D	3.250	3.450	0.128	0.135
D1	3.000	3.200	0.119	0.125
D2	1.780	1.980	0.070	0.077
D3	0.130 REF		0.005 REF	
E	3.200	3.400	0.126	0.133
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.011	0.019
L	0.300	0.500	0.011	0.019
L1	0.130 REF		0.005 REF	
K	0.300 REF		0.012 REF	
θ	0°	12°	0°	12°
M	0.150 REF		0.006 REF	